

1. General description

Planar passivated four quadrant triac in a SOT223 surface-mountable plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

2. Features and benefits

- High blocking voltage capability
- High noise immunity suitable for noisy applications
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants

3. Applications

- General purpose low power motor control
- General purpose switching and phase control

4. Quick reference data

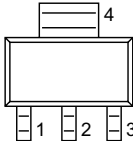
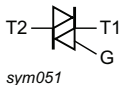
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Absolute maximum rating						
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{sp}} \leq 108\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$; $t_{\text{p}} = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	10	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$; $t_{\text{p}} = 16.7\text{ ms}$	-	-	11	A
T_{j}	junction temperature		-	-	125	°C
Static characteristics						
I_{GT}	gate trigger current	$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2+ G+; $T_{\text{j}} = 25\text{ °C}$; Fig. 9	-	5	35	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2+ G-; $T_{\text{j}} = 25\text{ °C}$; Fig. 9	-	8	35	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2- G-; $T_{\text{j}} = 25\text{ °C}$; Fig. 9	-	11	35	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2- G+; $T_{\text{j}} = 25\text{ °C}$; Fig. 9	-	30	70	mA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 11		-	5	15	mA
V_T	on-state voltage	$I_T = 2\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 12		-	1.2	1.5	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		100	250	-	V/ μs
dV_{com}/dt	rate of change of commutating voltage	$V_D = 400\text{ V}$; $T_j = 95\text{ }^\circ\text{C}$; $dI_{com}/dt = 1.8\text{ A/ms}$; $I_T = 1\text{ A}$; gate open circuit		-	50	-	V/ μs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		 sym051
2	T2	main terminal 2		
3	G	gate		
4	T2	main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BT134W-800	SOT223	BT134W-800,115	Reel	1000	SOT223	16-Mar-2006

7. Marking

Table 4. Marking codes

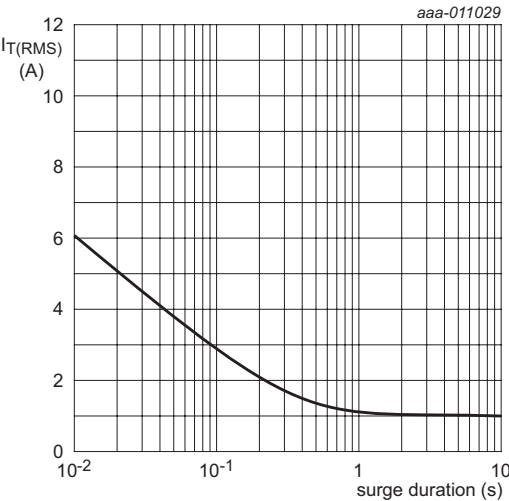
Type number	Marking codes	
	Assembly factory: L	Assembly factory: d
BT134W-800	JLxxx 80 BT134W	Jdxxx 80 BT134W

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{sp} \leq 108\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3		-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5		-	10	A
		full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 16.7\text{ ms}$		-	11	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN		-	0.5	A^2s
di_T/dt	rate of rise of on-state current	$I_G = 70\text{ mA}$		-	50	$\text{A}/\mu\text{s}$
				-	50	$\text{A}/\mu\text{s}$
		$I_G = 140\text{ mA}$		-	10	$\text{A}/\mu\text{s}$
		$I_G = 70\text{ mA}$		-	50	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current			-	2	A
P_{GM}	peak gate power			-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.5	W
T_{stg}	storage temperature			-40	150	$^{\circ}\text{C}$
T_j	junction temperature			-	125	$^{\circ}\text{C}$



$f = 50\text{ Hz}$; $T_{sp} \leq 108\text{ }^{\circ}\text{C}$

Fig. 1. RMS on-state current as a function of surge duration; maximum values

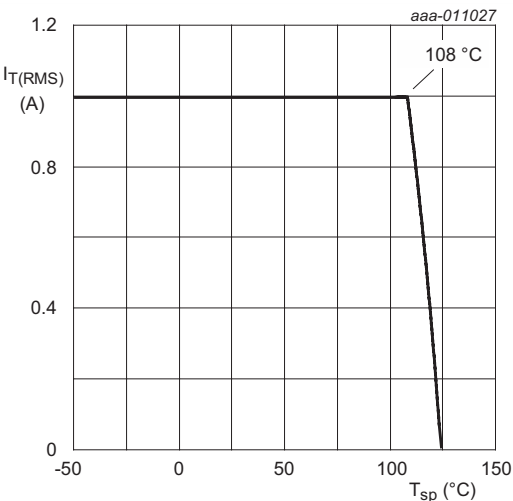
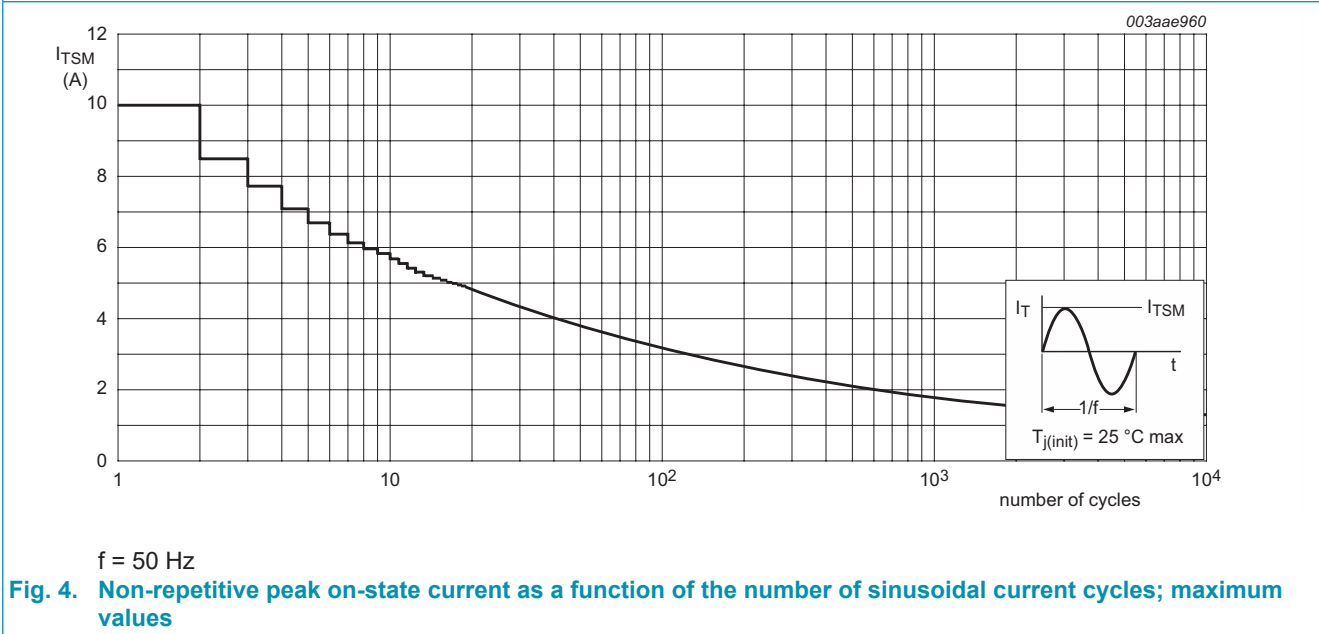
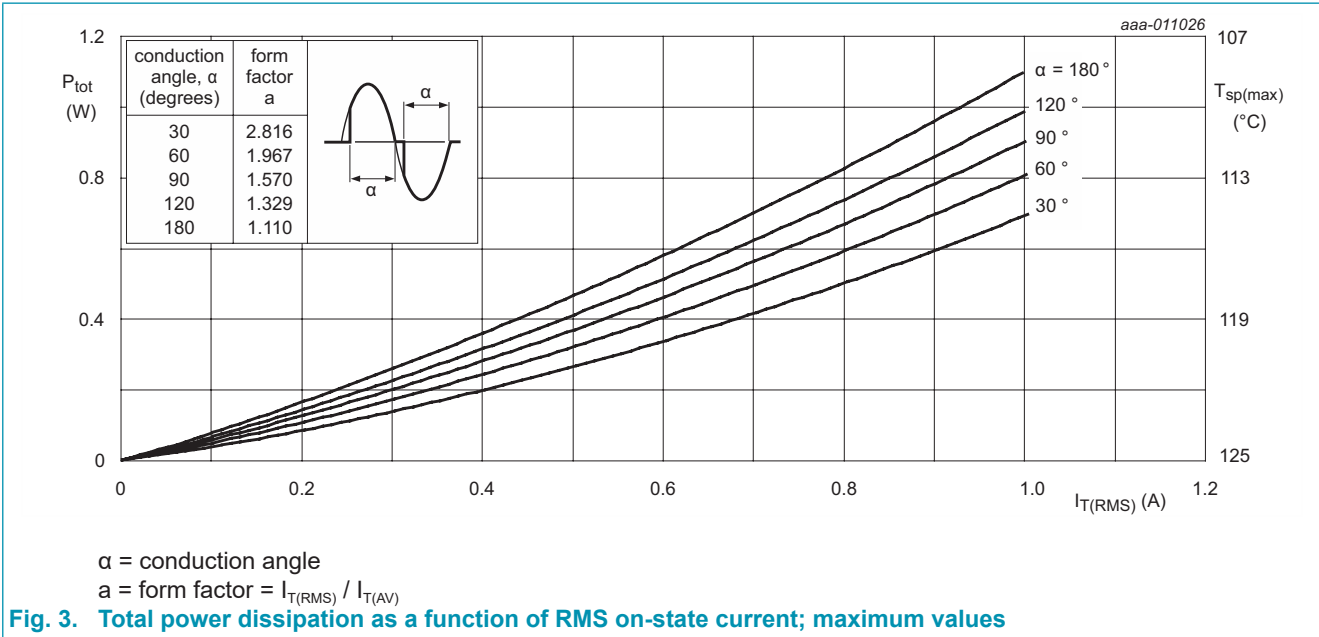
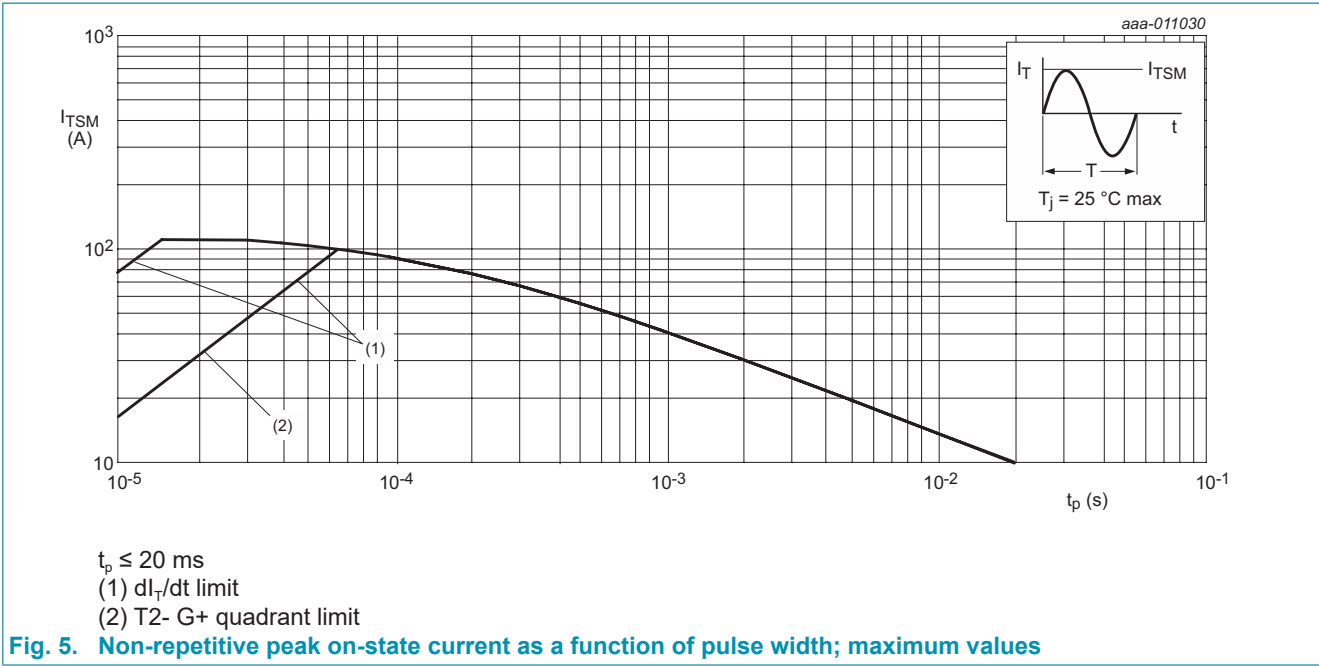


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values





9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	full cycle; Fig. 6		-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	full cycle; printed circuit board mounted; minimum footprint; Fig. 7		-	156	-	K/W
		full cycle; printed circuit board mounted; pad area; Fig. 8		-	70	-	K/W

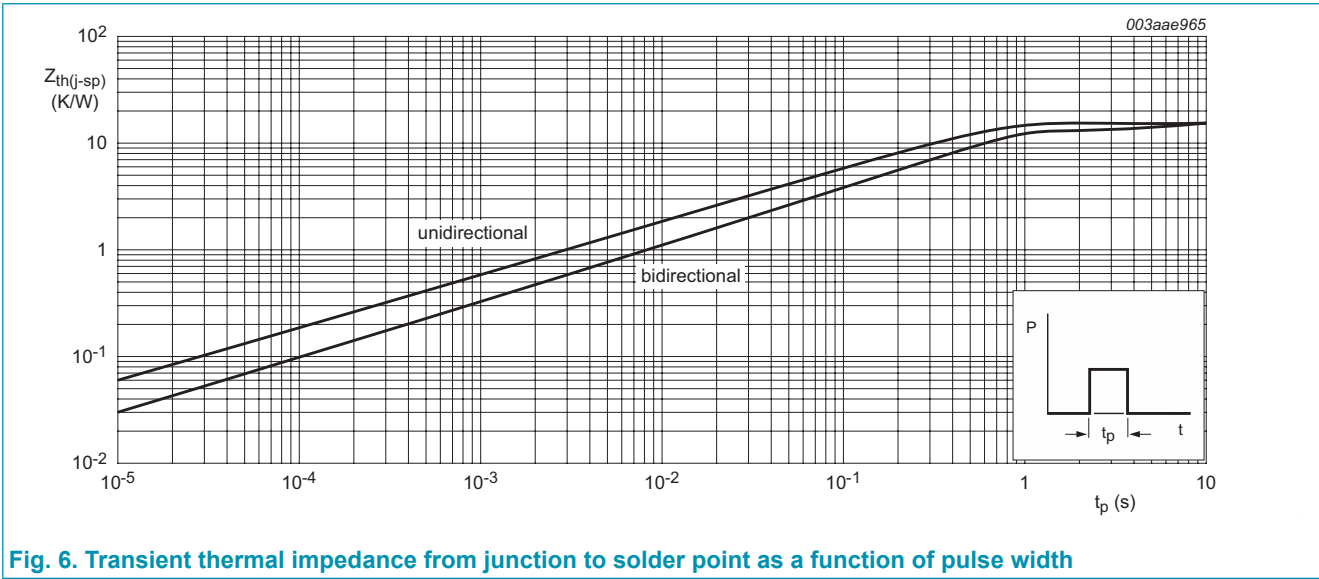
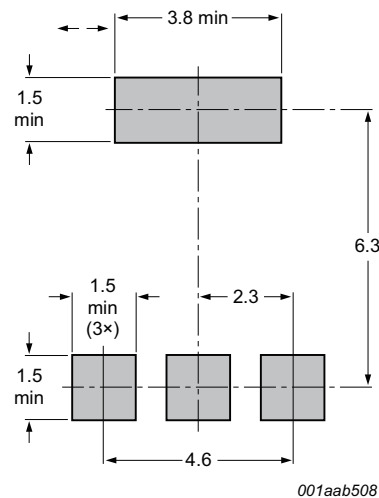
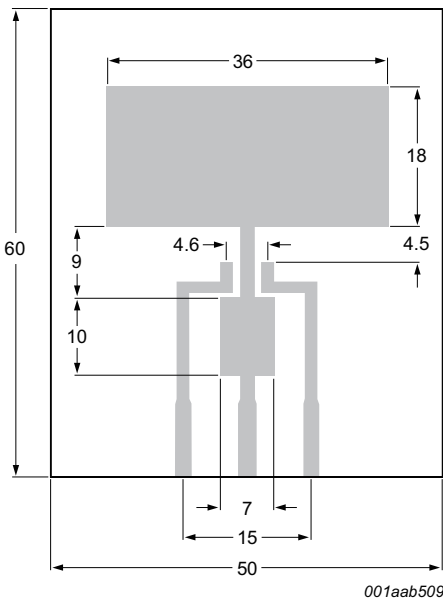


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width



All dimensions are in mm

Fig. 7. Minimum footprint SOT223



All dimensions are in mm

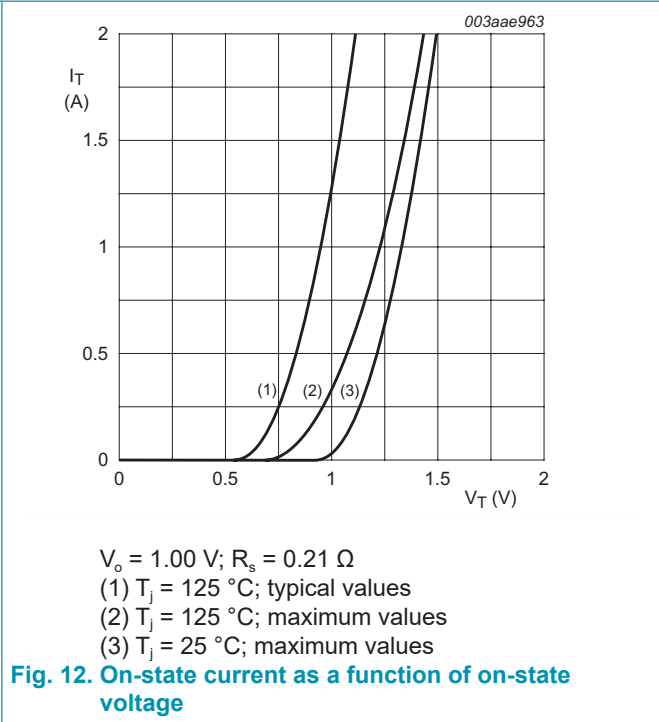
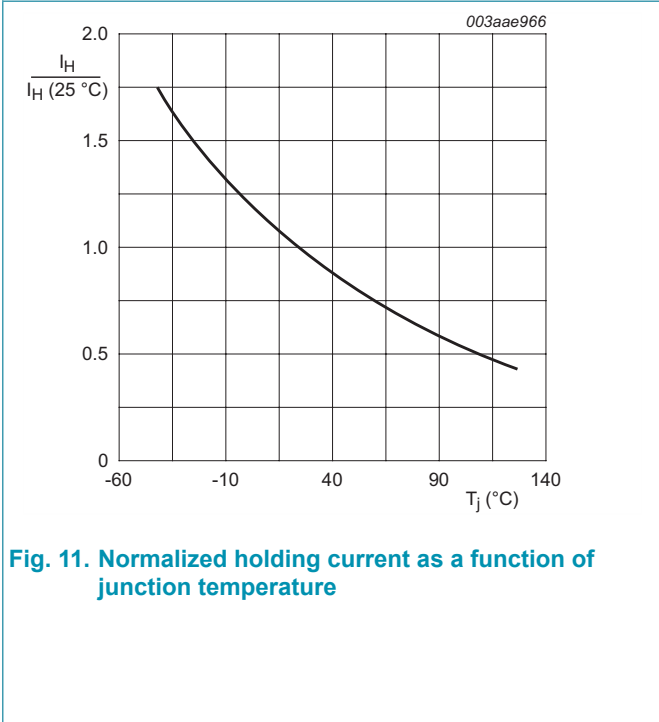
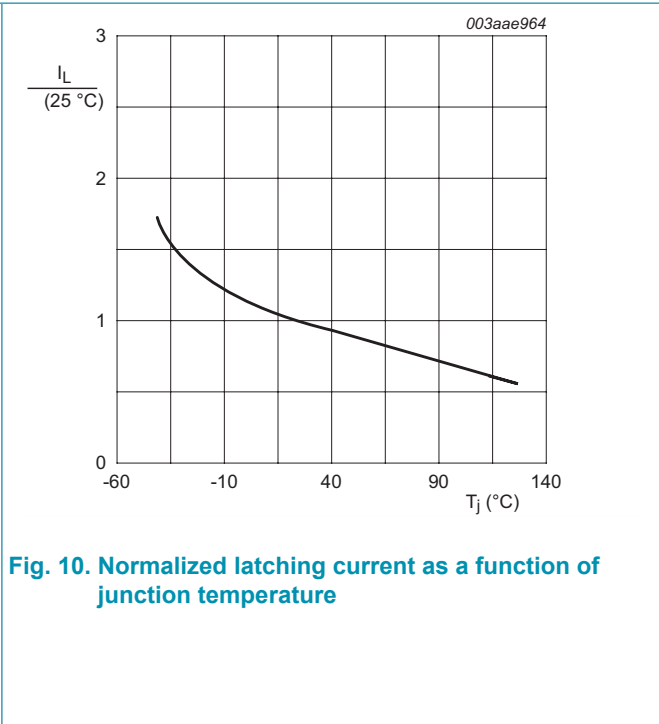
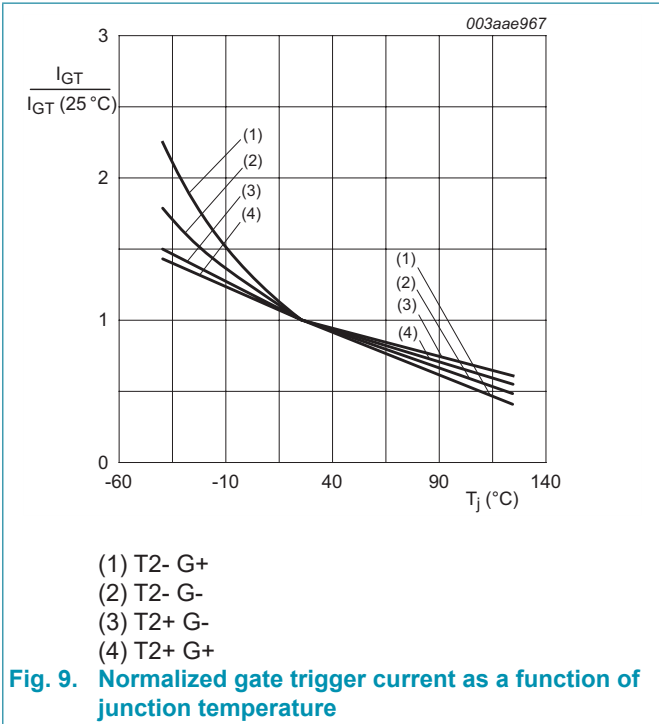
Printed circuit board:
FR4 epoxy glass (1.6 mm thick), copper laminate
(35 um thick)

Fig. 8. Printed circuit board pad area: SOT223

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 9		-	5	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 9		-	8	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 9		-	11	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 9		-	30	70	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 10		-	7	20	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 10		-	16	30	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 10		-	5	20	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 10		-	7	30	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 11		-	5	15	mA
V_T	on-state voltage	$I_T = 2\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 12		-	1.2	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 13		-	0.7	1	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 125\text{ }^\circ\text{C}$; Fig. 13		0.25	0.4	-	V
I_D	off-state current	$V_D = 800\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$		-	0.1	0.5	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		100	250	-	V/ μs
dV_{com}/dt	rate of change of commutating voltage	$V_D = 400\text{ V}$; $T_J = 95\text{ }^\circ\text{C}$; $dI_{com}/dt = 1.8\text{ A/ms}$; $I_T = 1\text{ A}$; gate open circuit		-	50	-	V/ μs
t_{gt}	gate-controlled turn-on time	$I_{TM} = 1.5\text{ A}$; $V_D = 800\text{ V}$; $I_G = 0.1\text{ A}$; $dI_G/dt = 5\text{ A}/\mu\text{s}$		-	2	-	μs



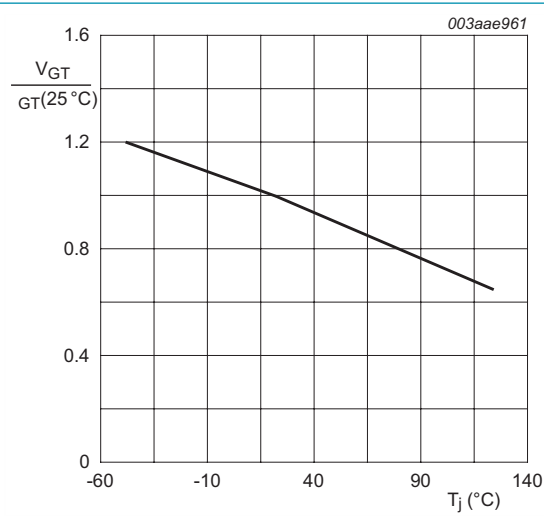


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

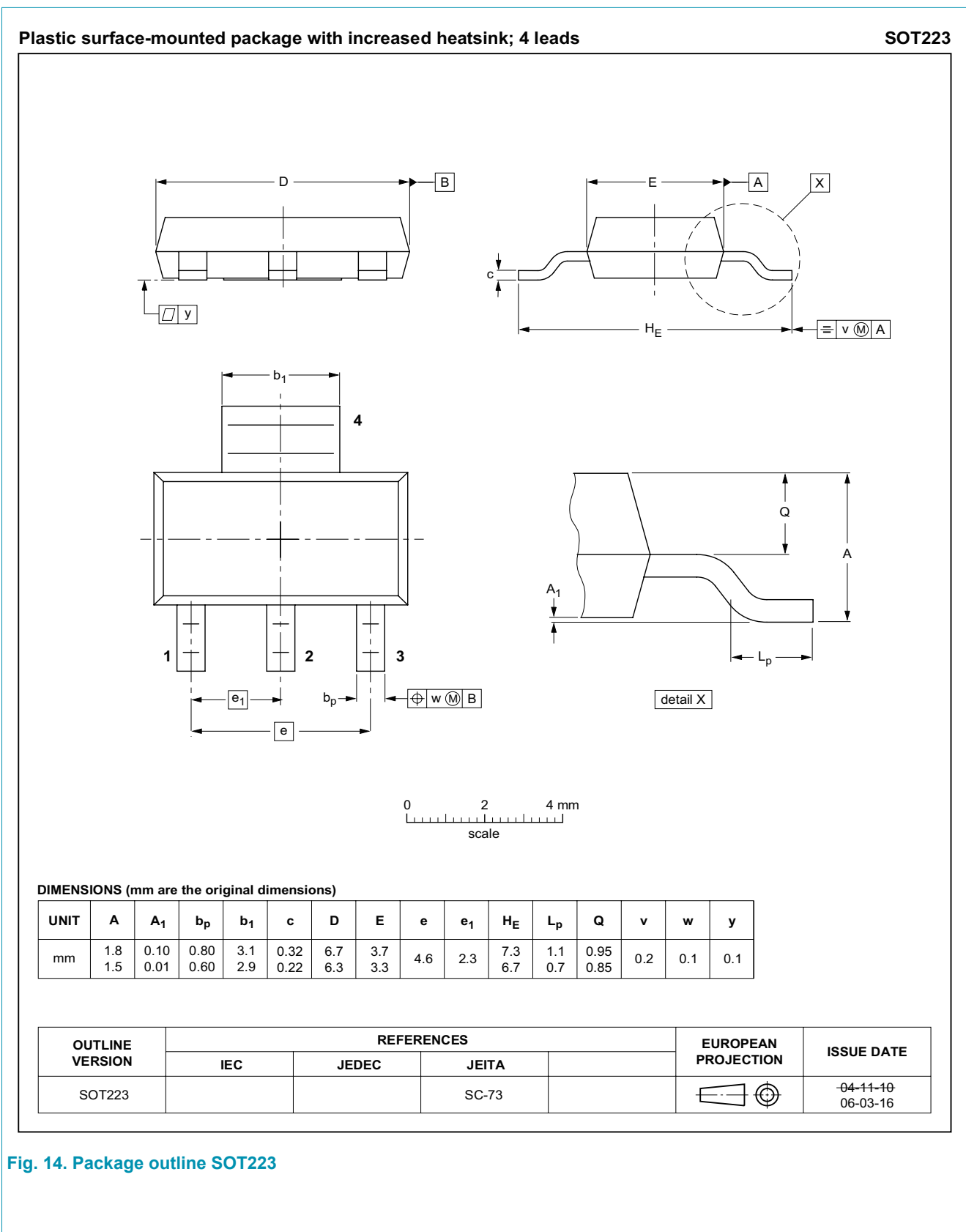


Fig. 14. Package outline SOT223

12. Soldering

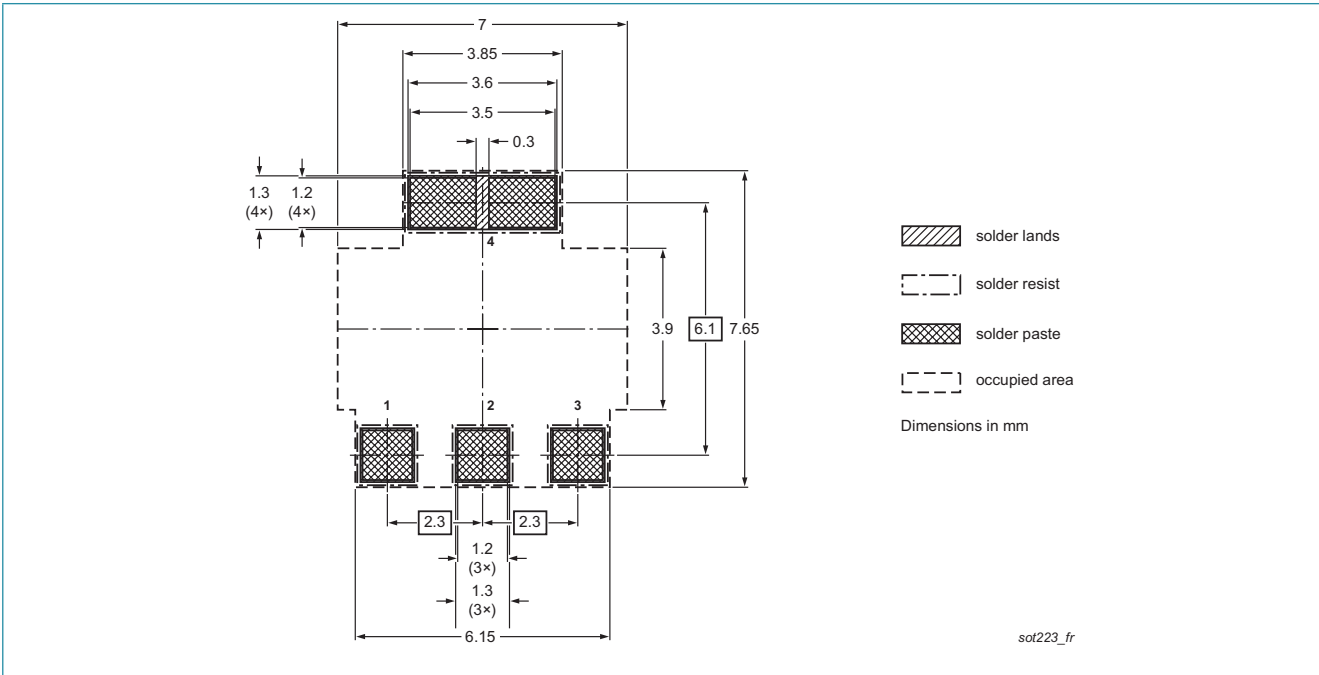


Fig. 15. Reflow soldering footprint for SC-73 (SOT223)

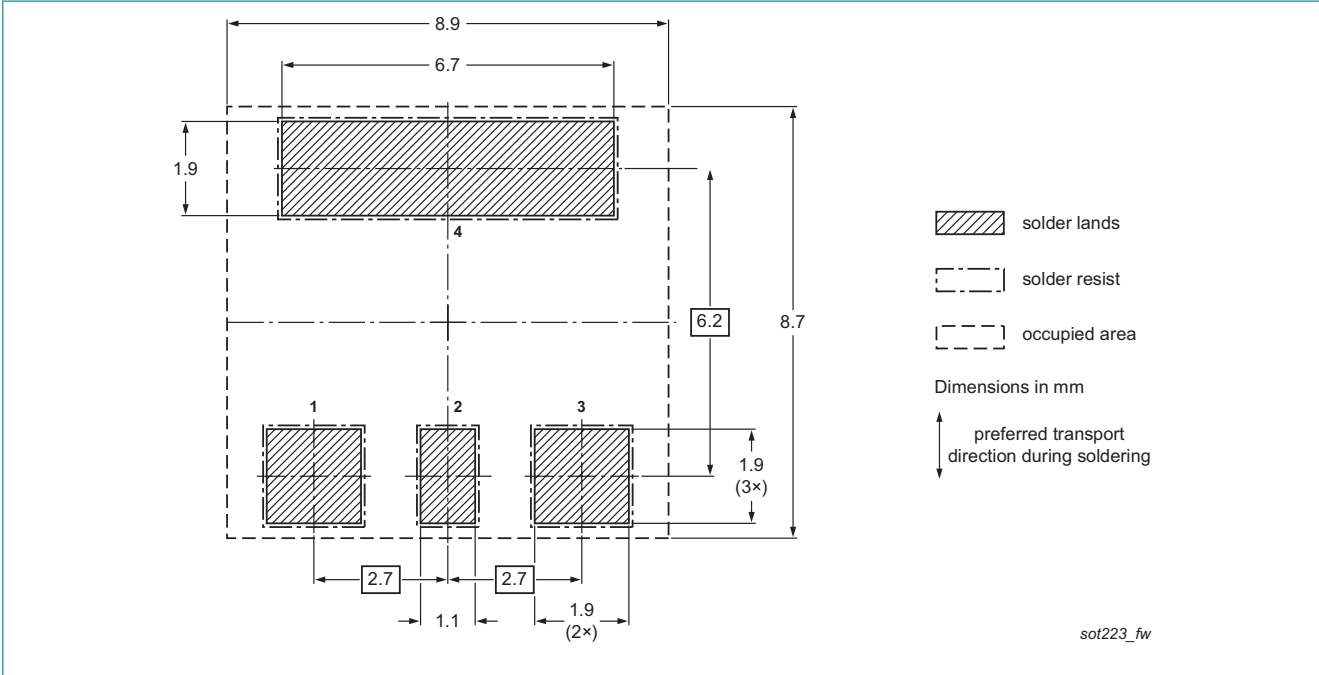


Fig. 16. Wave soldering footprint for SC-73 (SOT223)

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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